



# THE DATASHEET OF ZTX849



# ZTX849

## NPN SILICON PLANAR MEDIUM POWER HIGH CURRENT TRANSISTOR

ISSUE 2 – MARCH 94

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ )

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		850	950	mV	$I_C=5A, V_{CE}=1V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	100	200	300		$I_C=10mA, V_{CE}=1V$ $I_C=1A, V_{CE}=1V^*$ $I_C=5A, V_{CE}=1V^*$ $I_C=20A, V_{CE}=1V^*$
Transition Frequency	$f_T$		100		MHz	$I_C=100mA, V_{CE}=10V$ $f=50MHz$
Output Capacitance	$C_{obo}$		75		pF	$V_{CB}=10V, f=1MHz^*$
Switching Times	$t_{on}$ $t_{off}$		45 630		ns	$I_C=1A, I_B=100mA$ $I_B=100mA, V_{CE}=10V$

\*Measured under pulsed conditions. Pulse width=300 $\mu$ s. Duty cycle  $\leq$ 2%

### FEATURES

- \* 5 Amps continuous current
- \* Up to 20 Amps peak current
- \* Very low saturation voltages

### APPLICATIONS

- \* LCD backlight converter
- \* Flash gun converters
- \* Battery powered circuits
- \* Motor drivers

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	UNIT
Collector-Base Voltage	$V_{(BR)CBO}$	V
Collector-Emitter Voltage	$V_{(BR)CEO}$	V
Emitter-Base Voltage	$V_{(BR)EBO}$	V
Peak Pulse Current	$I_{CBP}$	A
Continuous Collector Current	$I_C$	A
Practical Power Dissipation*	$P_{tot}$	W
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	$P_{tot(25^{\circ}\text{C})}$	W
Operating and Storage Temperature Range	$T_{stg}$	$^{\circ}\text{C}$

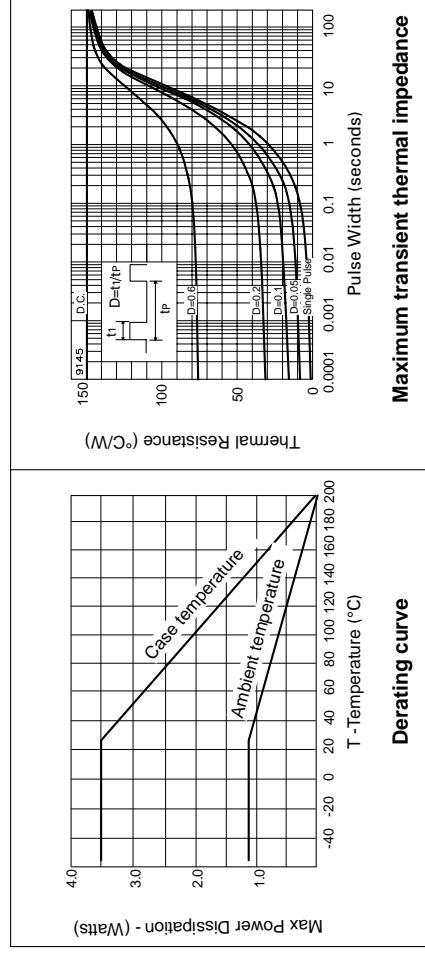
\*The power which can be dissipated as a function of ambient temperature. P.C.B. with copper equal to 1 inch square.

### ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	V
Collector Cut-Off Current	$I_{CBO}$	$\mu$ A
Collector Cut-Off Current	$I_{CER}$ $R_{\theta} \leq 1K\Omega$	$\mu$ A
Emitter Cut-Off Current	$I_{EBO}$	$\mu$ A
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	V

### THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient	$R_{\theta(j-amb)}$	150	$^{\circ}\text{C/W}$
Junction to Case	$R_{\theta(j-case)}$	50	$^{\circ}\text{C/W}$



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Static Forward Current Transfer Ratio	$h_{FE}$	100	200	300		$I_C=10mA, V_{CE}=1V$
		100	200			$I_C=1A, V_{CE}=1V^*$
		100	170			$I_C=5A, V_{CE}=1V^*$
		30	65			$I_C=20A, V_{CE}=1V^*$
Transition Frequency	$f_T$		100		MHz	$I_C=100mA, V_{CE}=10V, f=50MHz$
Output Capacitance	$C_{obo}$		75		pF	$V_{CB}=10V, f=1MHz^*$
Switching Times	$t_{on}$		45		ns	$I_C=1A, I_B=100mA$
	$t_{off}$		630		ns	$I_B=100mA, V_{CE}=10V$

\*Measured under pulsed conditions. Pulse width=300 $\mu$ s. Duty cycle  $\leq$ 2%

### THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient	$R_{\theta(j-amb)}$	150	$^{\circ}\text{C/W}$
Junction to Case	$R_{\theta(j-case)}$	50	$^{\circ}\text{C/W}$

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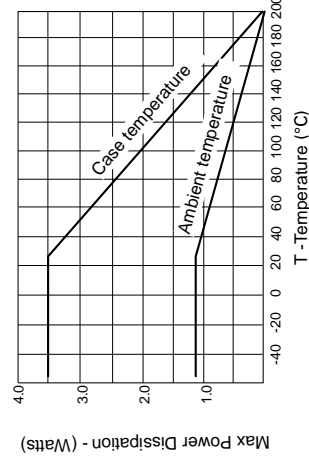
### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL
Collector-Base Voltage	$V_{(BR)CBO}$
Collector-Emitter Voltage	$V_{(BR)CEO}$
Emitter-Base Voltage	$V_{(BR)EBO}$
Peak Pulse Current	$I_{CBO}$
Continuous Collector Current	$I_{CER}$
Practical Power Dissipation*	$R \leq 1K\Omega$
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	$I_{EBO}$
Operating and Storage Temperature Range	$V_{CE(sat)}$

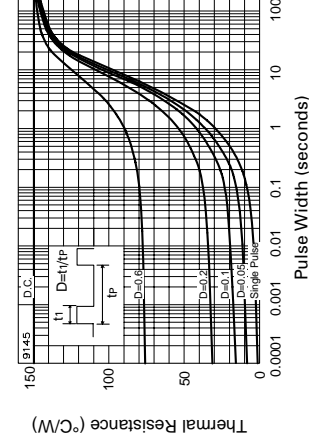
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### ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$
Collector Cut-Off Current	$I_{CBO}$
Collector Cut-Off Current	$I_{CER}$
Emitter Cut-Off Current	$I_{EBO}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$



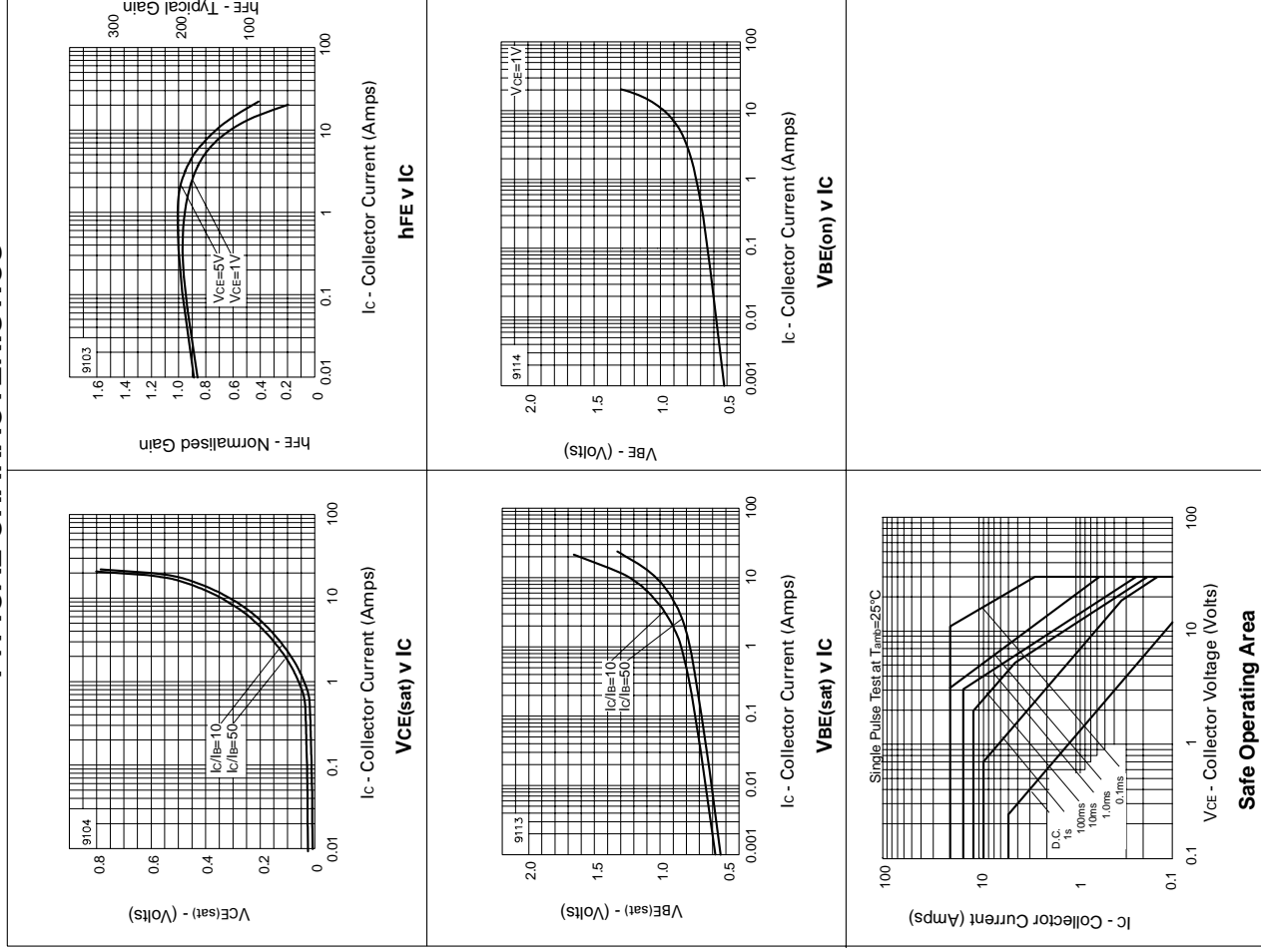
Derating curve



Maximum transient thermal impedance



# ZTX849

## TYPICAL CHARACTERISTICS



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